

Silicon NPN Power Transistors

2SD794 2SD794A

DESCRIPTION

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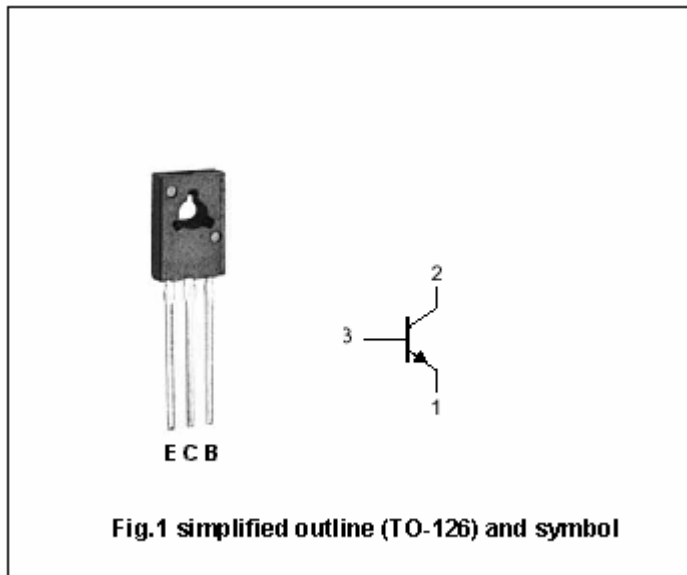
- With TO-126 package
- Complement to type 2SB744/744A
- High current 3A
- Excellent h_{FE} linearity

APPLICATIONS

- For use in audio frequency amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	70	V
V_{CEO}	Collector-emitter voltage	2SD794	45	V
		2SD794A	60	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		3	A
I_{CM}	Collector current-Peak		5	A
I_B	Base current (DC)		0.6	A
P_C	Collector power dissipation	$T_a=25^\circ$	1	W
		$T_C=25^\circ$	10	
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SD794	I _C =10mA; I _B =0	45			V
		2SD794A		60			
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.15A		0.3	2.0	V	
V _{BEsat}	Base-emitter saturation voltage	I _C =1.5A; I _B =0.15A		0.8	2.0	V	
I _{CBO}	Collector cut-off current	V _{CB} =45V; I _E =0			1	μA	
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			1	μA	
h _{FE-1}	DC current gain	I _C =20mA; V _{CE} =5V	30	70			
h _{FE-2}	DC current gain	I _C =0.5A; V _{CE} =5V	60	100	320		
f _T	Transition frequency	I _C =0.1A; V _{CE} =5V		60		MHz	
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V; I _E =0		40		pF	

◆ h_{FE-2} Classifications

R	O	Y
60-120	100-200	160-320

PACKAGE OUTLINE

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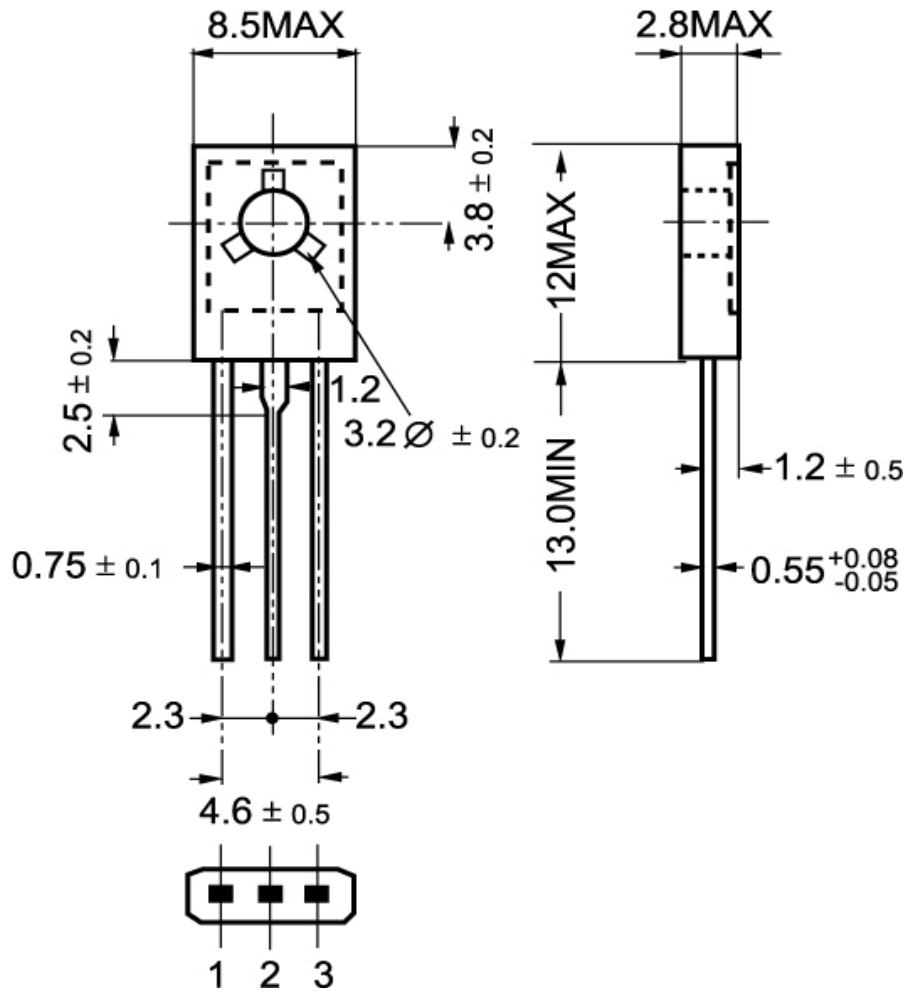


Fig.2 Outline dimensions